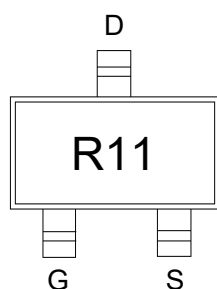


Features

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

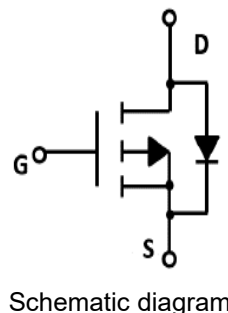
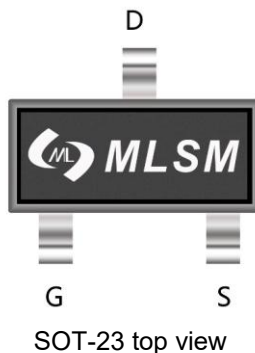


R11: Device code

Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-20V	36mΩ@-4.5V	-4.4A
	48mΩ@-2.5V	



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
--------	-----------	--------	------

Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±8	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-4.4	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	Tc=25°C	-15	A
I_D	Continuous Drain Current	Tc=25°C	-4.4	A
P_D	Maximum Power Dissipation	Tc=25°C	1.4	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		90	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS3411	SOT-23	R11	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±8V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	--	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-4.0A	--	36	45	mΩ
		V _{GS} =-2.5V, I _D =-4.0A	--	48	60	mΩ
		V _{GS} =-1.8V, I _D =-2.0A	--	63	85	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	606	--	pF
C _{OSS}	Output Capacitance		--	114	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	103	--	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-3.8A, V _{GS} =-10V	--	8.48	--	nC
Q _{gs}	Gate Source Charge		--	1.54	--	nC
Q _{gd}	Gate Drain Charge		--	2.61	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =-10V, I _D =-3.8A, V _{GS} =-4.5V, R _G =2.5Ω	--	5.8	--	nS
t _r	Turn-on Rise Time		--	34.8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	51.4	--	nS
t _f	Turn-Off Fall Time		--	52	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =-4.4A	--	--	-1.2	V

Typical Operating Characteristics

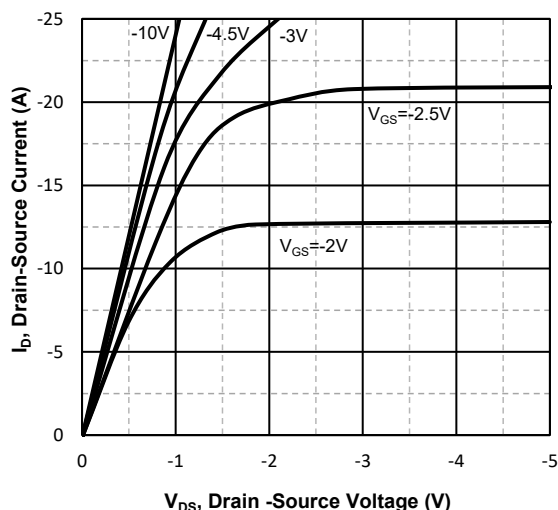


Fig1. Typical Output Characteristics

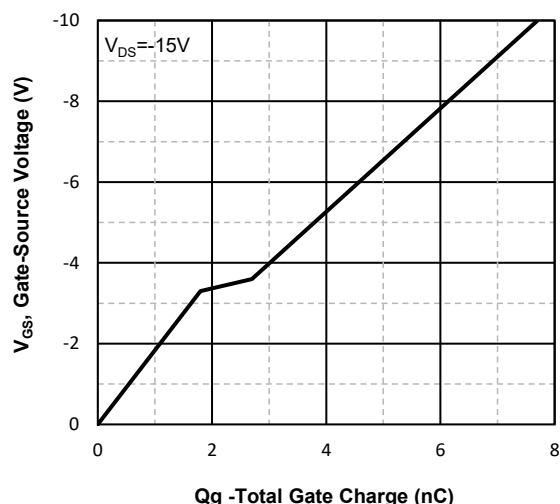


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

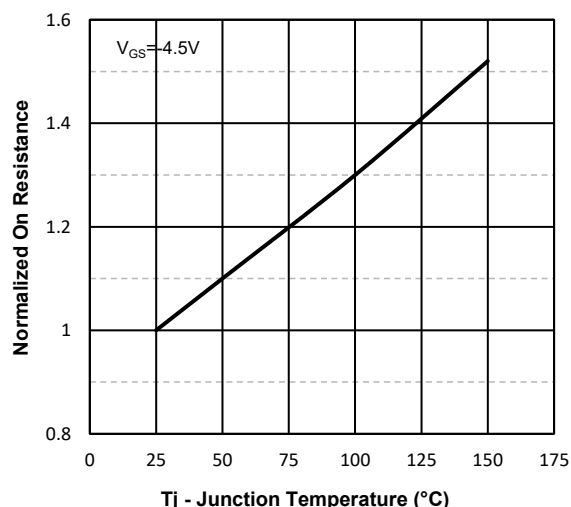


Fig3. Normalized On-Resistance Vs. Temperature

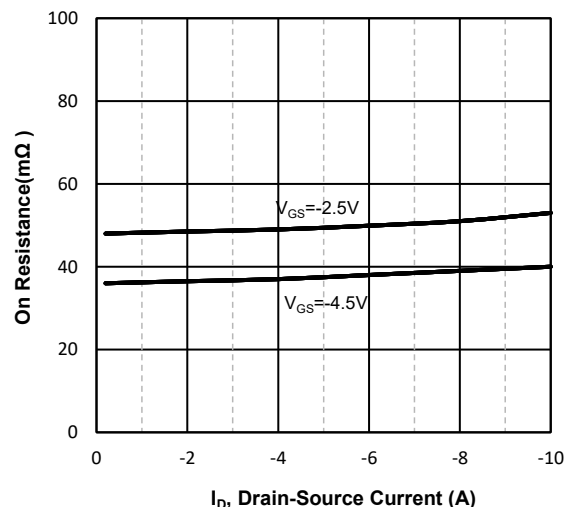


Fig4. On-Resistance Vs. Drain-Source Current

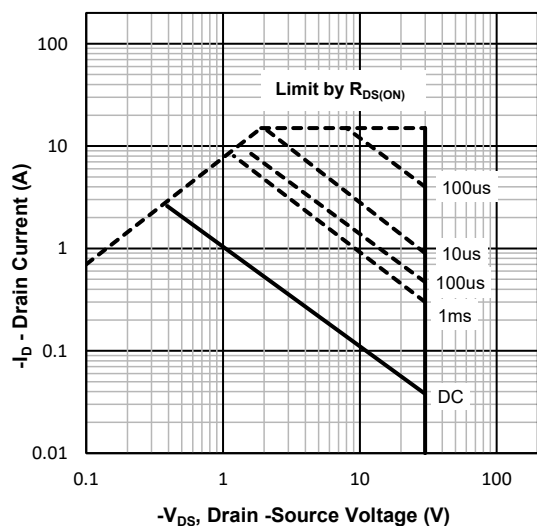


Fig5. Maximum Safe Operating Area

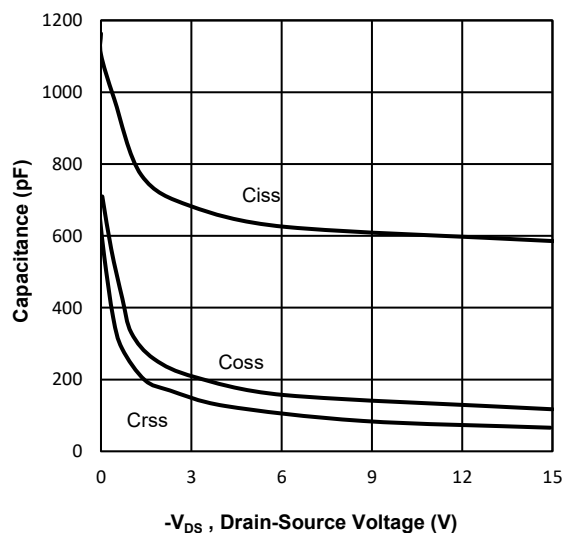
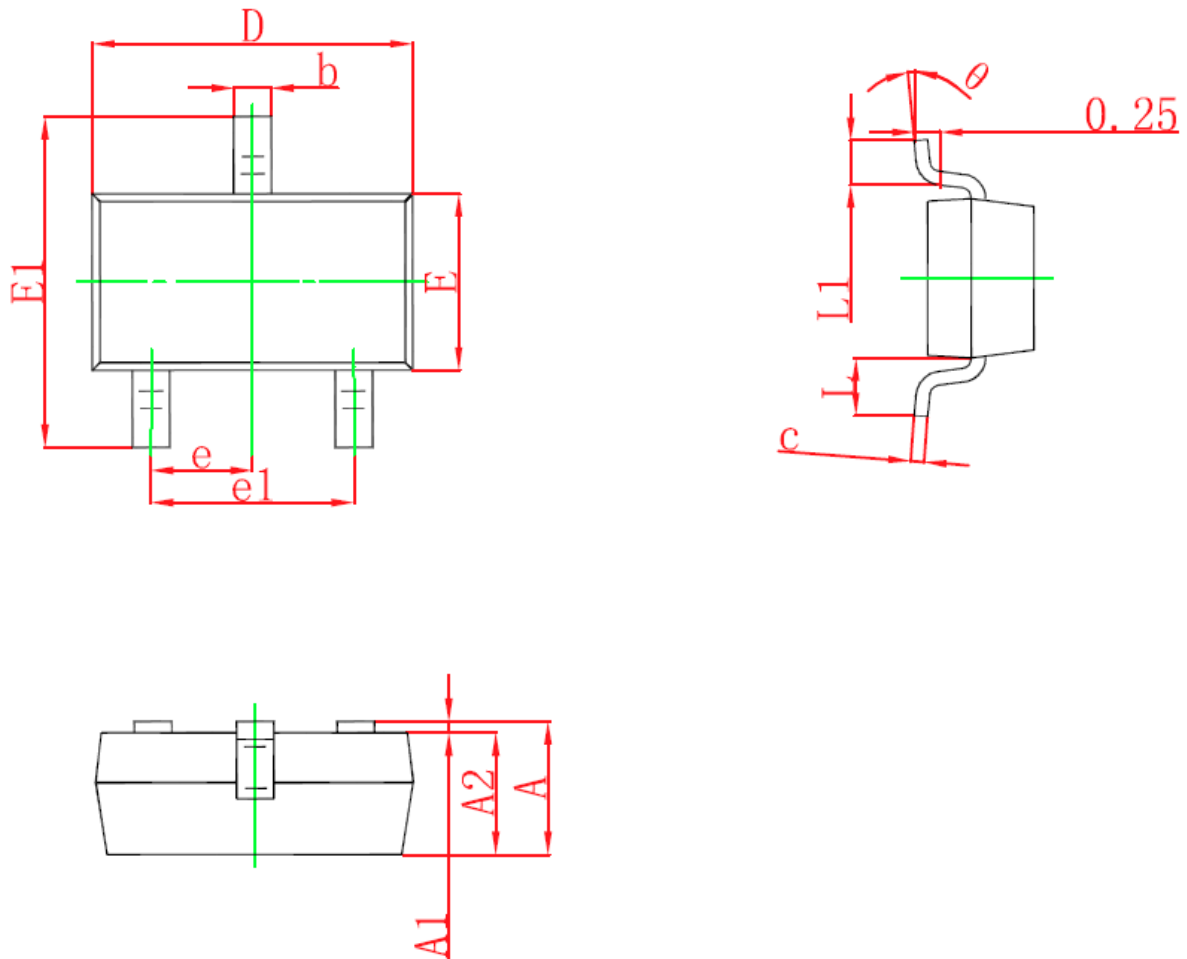


Fig6 Typical Capacitance Vs. Drain-Source

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°